

30V P-Channel Enhancement Mode MOSFET

Description

The CP100P03D6 uses advanced trench technology to provide excellent $R_{DS(ON)}$. This device is suitable for use as a load switch or in PWM applications.

General Features

- ◆ $V_{DS} = -30V$, $I_D = -100A$
 $R_{DS(ON)}(Typ.) = 3.3m\Omega$ @ $V_{GS} = -10V$
 $R_{DS(ON)}(Typ.) = 5m\Omega$ @ $V_{GS} = -4.5V$
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface mount package
- ◆ 150 °C operating temperature
- ◆ 100% UIS tested

Application

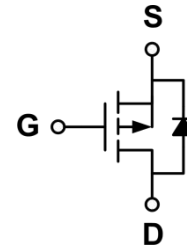
- ◆ PWM applications
- ◆ Load switch
- ◆ Uninterruptible power supply

Package

- ◆ PDFN5*6-8L-A

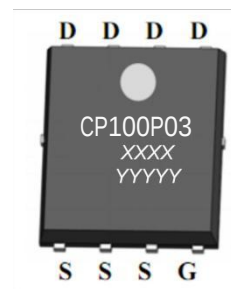


Schematic diagram

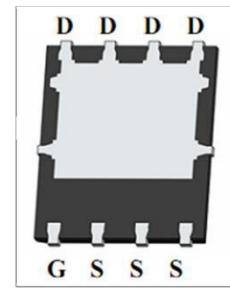


Marking and pin assignment

PDFN5*6-8L-A



Top View



Bottom View

XXXX—Wafer Information

YYYYY—Quality Code

Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
CP100P03D6-G	-55°C to +150°C	PDFN5*6-8L-A	5000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

parameter		symbol	limit	unit
Drain-source voltage		V_{DS}	-30	V
Gate-source voltage		V_{GS}	±20	V
Continuous Drain Current	TC=25°C	I_D	-100	A
	TC=70°C		-70	
Pulsed Drain Current		I_{DP}	-300	A
Avalanche energy (Tj=25°C, VDD=30V, VG=10V, L=0.5mH, Rg=25Ω)		E_{AS}	260	mJ
Power Dissipation	TC=25°C	P_D	80	W
	TC=70°C		50	
Operating junction Temperature range		Tj	-55—150	°C

Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-30	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	μA
		T _J =85°C	-	-	-10	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.6	-2.0	V
Drain-source on-state resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-30A	-	3.3	4	mΩ
		V _{GS} =-4.5V, I _D =-20A	-	5	6	
On Status Drain Current	I _{D(ON)}	V _{DS} =-15V, V _{GS} =-10V	-50	-	-	A
Diode Characteristics						
Diode Forward Voltage	V _{SD}	I _{SD} =-20A, V _{GS} =0V	-	-0.6	-1.2	V
Diode Continuous Forward Current	I _S		-	-100	-	A
Reverse Recovery Time	t _{rr}	I _F =-30A,	-	90	-	ns
Reverse Recovery Charge	Q _{rr}	di/dt=-100A/us	-	210	-	nC
Dynamic Characteristics						
Gate Resistance	R _G	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	5.5	-	Ω
Input capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =-15V f=1.0MHz	-	6932	-	pF
Output capacitance	C _{OSS}		-	845	-	
Reverse transfer capacitance	C _{RSS}		-	804	-	
Turn-on delay time	t _{D(ON)}	V _{GS} =-10V, V _{DS} =-15V, R _L =3Ω, I _D =-1A, R _G =2.5Ω	-	7	-	ns
Turn-on Rise time	t _r		-	9.4	-	
Turn-off delay time	t _{D(OFF)}		-	30	-	
Turn-off Fall time	t _f		-	13	-	
Total gate charge	Q _g	V _{GS} =-10V, I _D =-30A V _{DS} =-15V	-	133	-	nC
Gate-source charge	Q _{gs}		-	20.5	-	
Gate-drain charge	Q _{gd}		-	24.3	-	

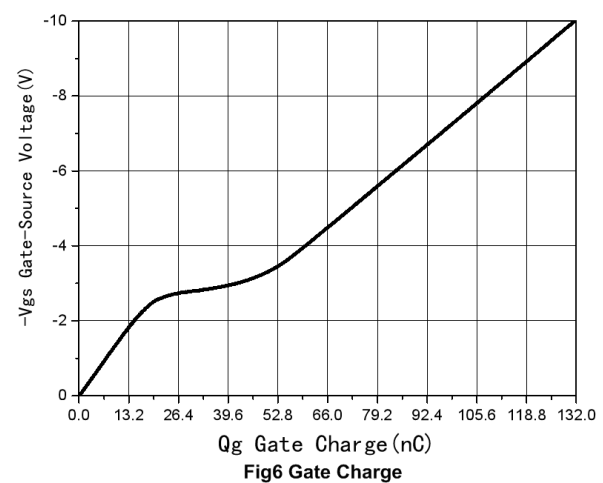
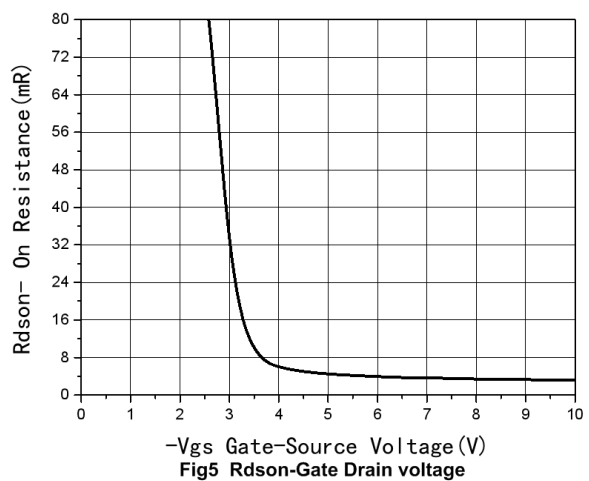
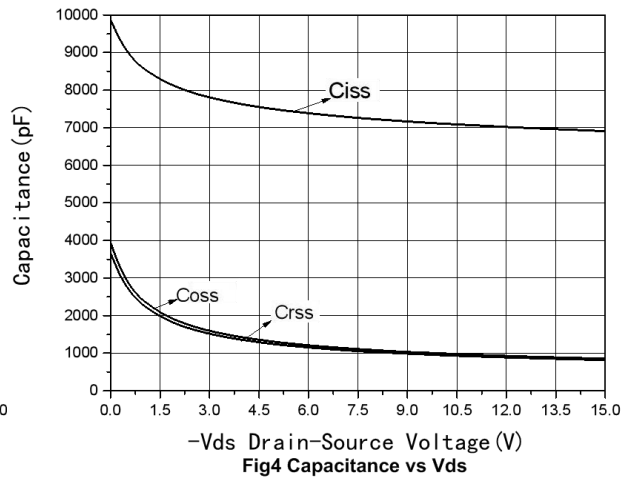
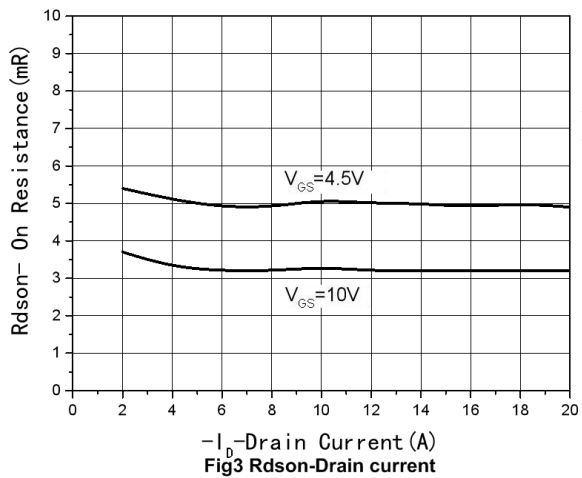
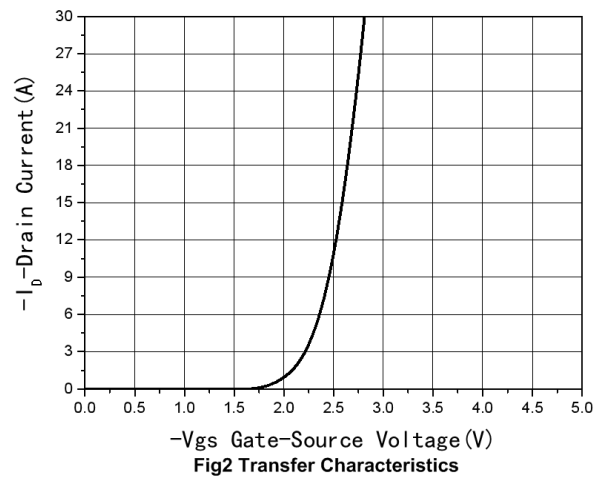
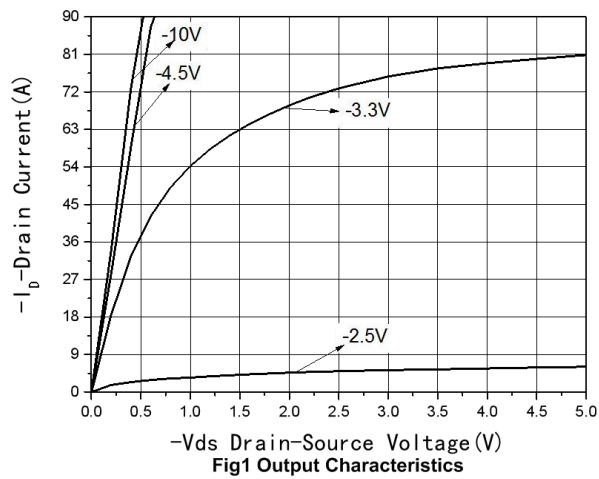
Thermal Characteristics

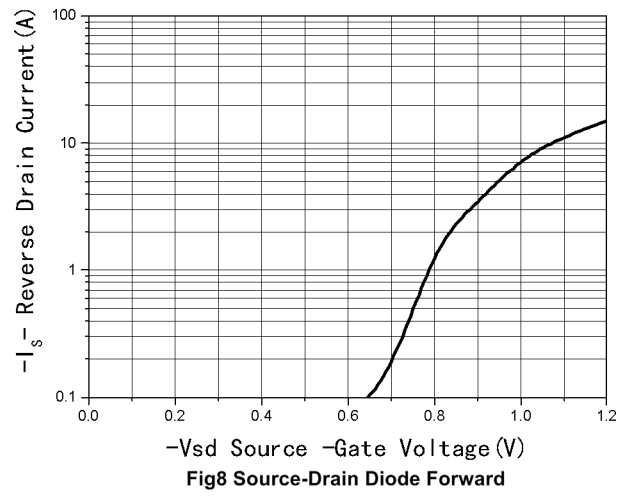
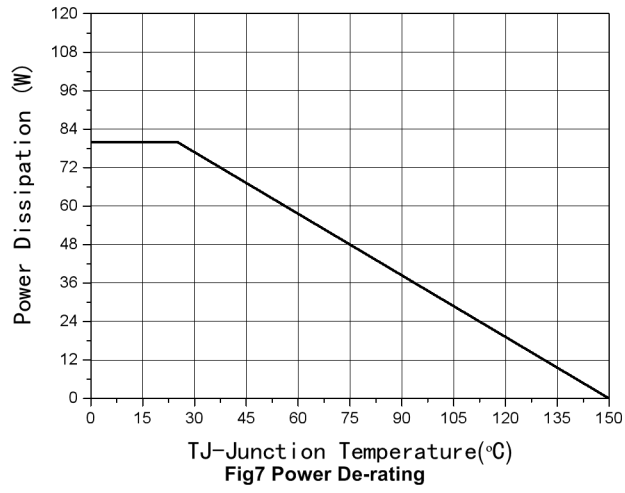
Parameter	Symbol	Typ	Max	Unit
Maximum Junction-to-Ambient ^A	R _{θJA}	27	35	°C/W
Maximum Junction-to-Ambient ^A		55	63	
Maximum Junction-to-Lead ^B	R _{θJC}	3.3	4	

A: The value of R_{θJA} is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

Typical Performance Characteristics

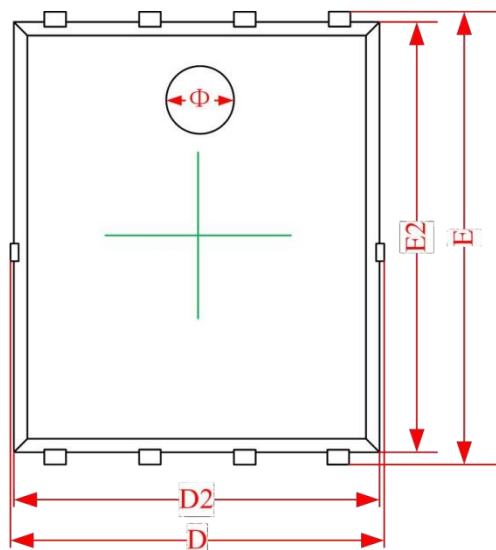




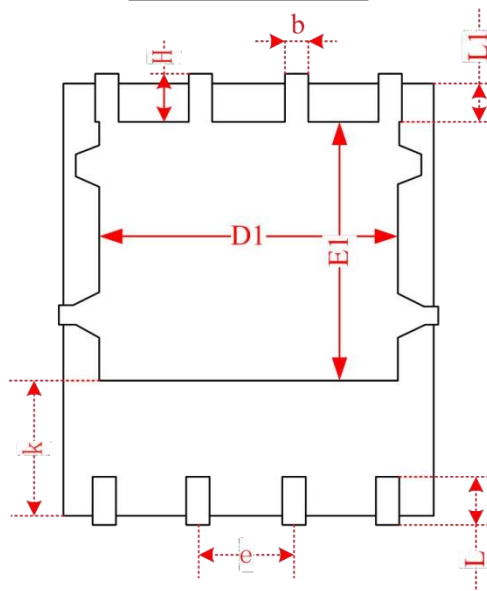
Package Information

- PDFN5*6-8L-A

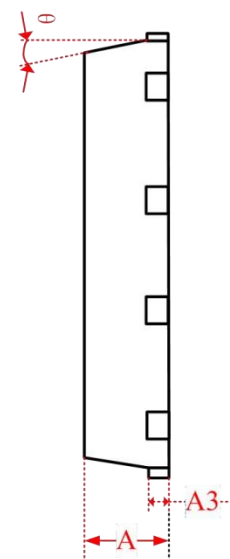
Top View



Bottom View



Side View



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.870	0.900	0.930	0.034	0.035	0.036
A3	0.203REF.			0.008REF.		
D	4.944	5.020	5.096	0.195	0.198	0.201
E	5.974	6.050	6.126	0.235	0.238	0.241
D1	3.910	4.010	4.110	0.154	0.158	0.162
E1	3.375	3.475	3.575	0.133	0.137	0.141
D2	4.870	4.900	4.930	0.192	0.193	0.194
E2	5.720	5.750	5.780	0.226	0.227	0.228
k	1.190	1.290	1.390	0.047	0.051	0.055
b	0.350	0.380	0.410	0.014	0.015	0.016
e	1.270TYP.			0.050TYP.		
L	0.559	0.635	0.711	0.022	0.025	0.028
L1	0.424	0.500	0.576	0.017	0.020	0.023
H	0.574	0.650	0.726	0.023	0.026	0.029
θ	10°	11°	12°	10°	11°	12°
Φ	1.150	1.200	1.250	0.045	0.047	0.049